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(71) Applicant: **LAM RESEARCH CORPORATION**
[US/US]; 4650 Cushing Parkway, Fremont, CA 94538
(US).

(72) Inventor: **BOYD, John, M.**; 8730 Sierra Vista Road,
Atascadero, CA 93422 (US).

(74) Agent: **BECKER, Donna, E.**; Brinks Hofer Gilson & Li-
one, P.O. Box 10087, Chicago, IL 60610 (US).

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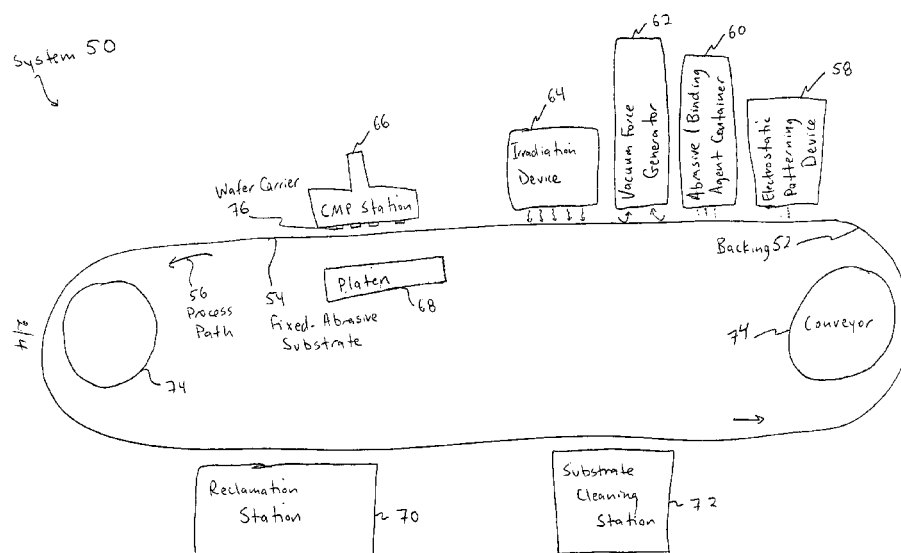
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(54) Title: METHOD AND APPARATUS FOR FIXED-ABRASIVE SUBSTRATE MANUFACTURING AND WAFER POLISH-
ING IN A SINGLE PROCESS PATH



(57) Abstract: Methods and apparatus are provided for combining the manufacturing of a fixed-abrasive substrate and the chemical mechanical planarization of semiconductor wafers using a single process path (26). An electrostatic patterning device (58) produces an electrostatic charge of a predetermined pattern and density on a backing (52). An abrasive/binding agent container (60) deposits an abrasive/binding agent mixture on the surface of the backing (52). The mixture is attracted to the backing (52) in the pattern of the electrostatic charge. A vacuum force generator (62) removes the excess abrasive/binding agent mixture from the backing (52). An UV irradiation device (64) fixes the mixture to the backing (52). A conveyor (74) carries the fixed-abrasive substrate (54) to the CMP station (66).